Iridium Etching: Exploring Reactive Ion Etching Parameters for Efficient Electrode Fabrication in Ferroelectric Memory

Y. N. Li[1], P. Bézard[2], X. Y. Piao[2], R. Blanc[2], Y. Canvel[2], S. Kundu[2] and F. Lazzarino[2]

[1] Imec, Kapeldreef 75, 3001 Heverlee, Belgium

Non-volatile Ferroelectric lead zirconium titanate (PZT) are interesting candidates for future memory applications but the fatigue resistance of the electrode material from the capacitors is a challenge. Iridium (Ir) is being investigated as electrode material for its superior characteristic. Thus, a patterning process must be developed. Due to the low volatility of the etch products, etching Ir is typically performed by ion beam etching (IBE). The low-throughput, relative scarcity of IBE chambers in the industry, as well as the limited tunability of the sputtering process are motivations for the development of a plasma-based etching approach.

In this work, we conducted experiments with TiN as a hard mask, following the process flow shown in Figure 1. Preliminary data indicates that Ir can be etched using both fluorine-based and chlorine-based gases. We identify and highlight the primary parameters affecting the Ir etch rate in the RIE process, focusing on gas flow rates, power settings, pressure, and substrate temperature. We also compare the relative contributions of physical and chemical reactions to the etch rate of Ir.

XSEM pictures for those experiments are shown in figures 2 and 3. It is observed that selectivity with a TiN hard-mask is a challenge when using these chemistries. Sidewall residues have also been observed in conditions where ion sputtering is dominant. Therefore, optimization of the etch processes based upon an understanding of the etch mechanisms in place is necessary.

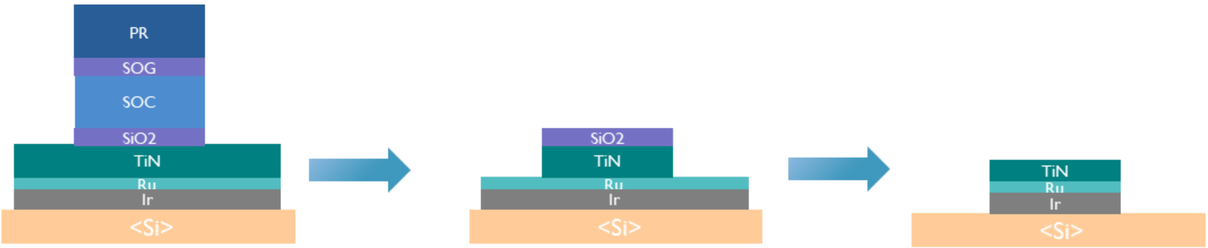

Figure 1 Process flow of Ir etching. Using TiN as a hard mask to etch Ir.

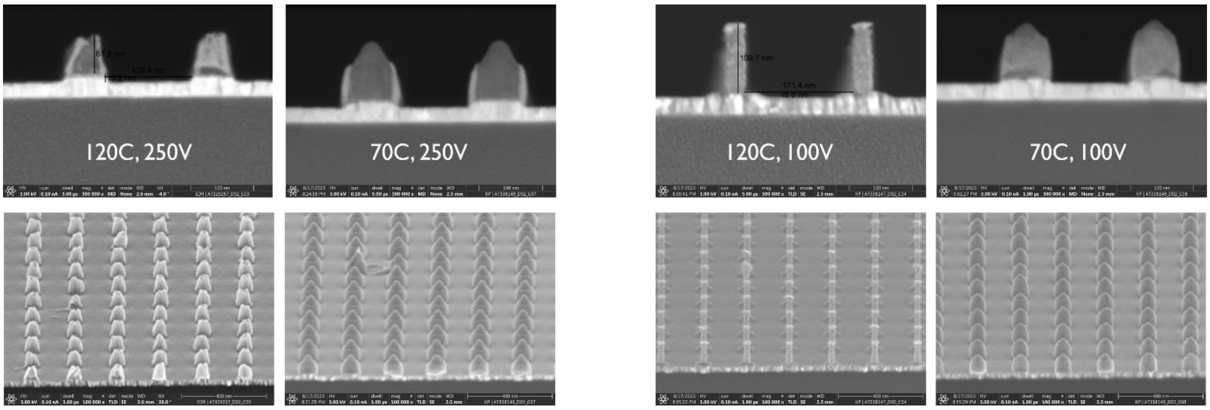

Figure 2 The profile of HM and Ir with different temperatures and bias powers.

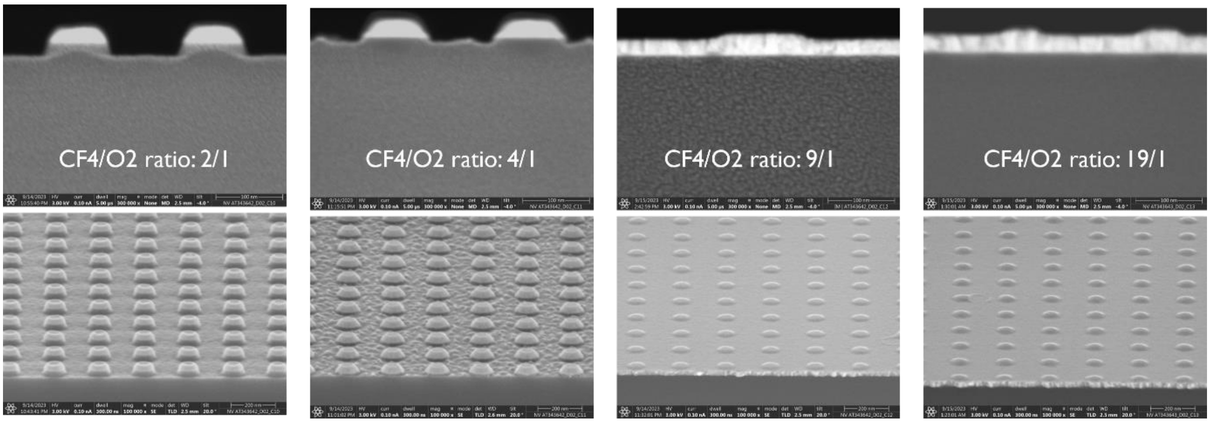

Figure 3 The profile of HM and Ir with different gas ratio of CF4 and O2.